

SPECIFICATION AMENDMENTS:

Please amend the specification as follows:

Page 10, line 18, through line 28, please amend the current paragraph as follows:

The n-type GaAs layer 111 has a thickness of about 10nm (= 0.01 μm), the n-type $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer 112 has a thickness of about 0.5 μm , the n-type $\text{Al}_y\text{Ga}_{1-y}\text{As}$ layer 113 has a thickness of about 1 μm , and the n-type $\text{Al}_z\text{Ga}_{1-z}\text{As}$ layer 114 has a thickness of about 0.5 μm . In this case, the thickness of the LED epitaxial film 110 becomes about 2 μm . However, the thicknesses of the above layers are not limited to the above values. Further, the material of the LED epitaxial film 110 may be replaced by other material, e.g., a compound semiconductor, such as $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$, where $0 \leq x \leq 1$ and $0 \leq z \leq 1$, in this case, GaN, AlGaIn, or InGaIn.